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BT
5-22-02

TSMC-01-144

May 3, 2002

To: Commissioner of Patents and Trademarks
Washington, D.C. 20231

Fr: George O. Saile, Reg. No. 19,572
20 McIntosh Drive
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Subject: Serial No. 10/086,258 03/04/02

Ming-Hwa Yoo, Shih-Chi Lin,
Yi-Lung Cheng, Szu-An Wu,
Ying-Lang Wang

A NOVEL METHOD TO SOLVE IMD-FSG PARTICLE AND INCREASE Cp YIELD BY USING A NEW TOUGHER UFUN SEASON FILM

Grp. Art Unit: 1763

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation In An Application.

The following Patents and/or Publications are submitted to comply with the duty of disclosure under CFR 1.97-1.99 and 37 CFR 1.56. Copies of each document is included herewith.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner of Patents and Trademarks, Washington, D.C. 20231, on May 14, 2002.

Stephen B. Ackerman, Reg.# 37761

Signature/Date 5/14/02

U.S. Patent 5,983,906 to Zhao et al., "Methods and Apparatus for a Cleaning Process in a High Temperature, Corrosive, Plasma Environment," describes systems, methods and apparatus for depositing titanium films at rates of up to 200 A/minute on semiconductor substrates from a titanium tetrachloride source.

U.S. Patent 6,020,035 to Gupta et al., "Film to Tie Up Loose Fluorine in the Chamber After a Clean Process," describes an undoped silicate glass (USG) seasoning film and process.

U.S. Patent 5,811,356 to Murugesh et al., "Reduction in Mobile Ion and Metal Contamination by Varying Season Time and Bias RF Power During Chamber Cleaning," describes a method and apparatus for reducing the concentration of mobile ion and metal contaminants in a processing chamber.

U.S. Patent 6,121,161 to Rossman et al., "Reduction of Mobile Ion and Metal Contamination in HDP-CVD Chambers Using Chamber Seasoning Film Depositions," describes a method and apparatus for controlling the introduction of contaminates into a deposition chamber that occur naturally within the chamber components.

U.S. Patent 6,136,211 to Qian et al., "Self-Cleaning Etch Process," describes a self-cleaning etch process whereby during etching of a substrate in an etching chamber, a thin non-homogeneous etch residue deposited on the surfaces of the walls and components of the etching chamber are simultaneously cleaned.

U.S. Patent 5,705,080 to Leung et al., "Plasma-Inert Cover and Plasma Cleaning Process," describes a plasma-inert cover and plasma cleaning process.

Sincerely,

Stephen B. Ackerman,
Reg. No. 37761

Form PTO-1449

INFORMATION DISCLOSURE CITATION IN AN APPLICATION

(Use several sheets if necessary)

Docket Number (Optional)	Application Number
TSMC-01-144	10/086,258
Applicant: Ming-Hwa Yoo et al.	
Filing Date: 03/04/02	Group Art Unit: 1763

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	6020035	2/1/00	Gupta et al.	427	534	10/29/96
	5811356	9/22/98	Murugesh et al.	438	711	8/19/96
	5983906	11/16/99	Zhao et al.	134	1.1	8/22/97
	6121161	9/19/00	Rossman et al.	438	783	1/19/99
	6136211	10/24/00	Qian et al.	216	37	11/12/97
	5705080	1/6/98	Leung et al.	216	67	7/6/94

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation YES	Translation NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER	DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.